

TOSHIBA Photocoupler GaAlAs Ired & Photo-IC

TLP2200

Isolated Buss Driver

High Speed Line Receiver

Microprocessor System Interfaces

MOS FET Gate Driver

Direct Replacement For HCPL-2200

The TOSHIBA TLP2200 consists of a GaAlAs light emitting diode and integrated high gain, high speed photodetector.

This unit is 8-lead DIP package.

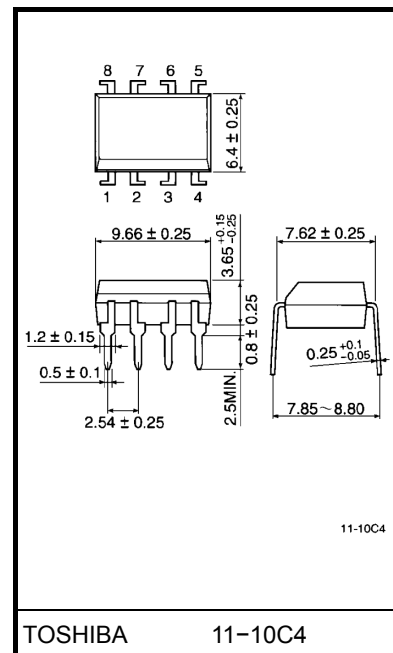
The detector has a three state output stage that eliminates the need for pull-up resistor, and built-in schmitt trigger. The detector IC has an internal shield that provides a guaranteed common mode transient immunity of 1000V / μ s.

- Input current: $I_F = 1.6\text{mA}$
- Power supply voltage: $V_{CC} = 4.5\sim 20\text{V}$
- Switching speed: 2.5MBd guaranteed
- Common mode transient immunity: $\pm 1000\text{V} / \mu\text{s}$ (min.)
- Guaranteed performance over temp: $0\sim 85^\circ\text{C}$
- Isolation voltage: 2500Vrms(min.)
- UL recognized: UL1577, file No. E67349

Truth Table (positive logic)

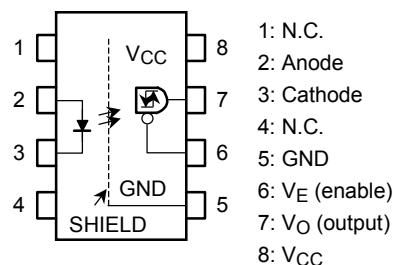
Input	Enable	Output
H	H	Z
L	H	Z
H	L	H
L	L	L

Unit in mm

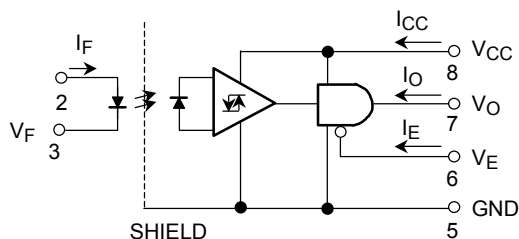


Weight: 0.54 g

Pin Configuration (top view)



Schematic



Recommended Operating Conditions

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Input current, on	$I_{F(ON)}$	1.6	—	5	mA
Input current, off	$I_{F(OFF)}$	0	—	0.1	mA
Supply voltage	V_{CC}	4.5	—	20	V
Enable voltage high	V_{EH}	2.0	—	20	V
Enable voltage low	V_{EL}	0	—	0.8	V
Fan out (TTL load)	N	—	—	4	—
Operating temperature	T_{opr}	0	—	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Absolute Maximum Ratings (no derating required up to 70°C)

Characteristic		Symbol	Rating	Unit
D E L	Forward current	I_F	10	mA
	Peak transient forward current (Note 1)	I_{FPT}	1	A
	Reverse voltage	V_R	5	V
T o t a l P a c k a g e	Output current	I_O	25	mA
	Supply voltage	V_{CC}	−0.5~20	V
	Output voltage	V_O	−0.5~20	V
	Three state enable voltage	V_E	−0.5~20	V
	Total package power dissipation (Note 2)	P_T	210	mW
	Operating temperature range	T_{opr}	−40~85	°C
Storage temperature range		T_{stg}	−55~125	°C
Lead solder temperature (10s) (**)		T_{sol}	260	°C
Isolation voltage (AC 1min., R.H. ≤ 60%, $T_a = 25^\circ\text{C}$) (Note 3)		BV_S	2500	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 1) Pulse width 1μs 300pps.

(Note 2) Derate 4.5mW / °C above 70°C ambient temperature.

(Note 3) Device considered a two terminal device: Pins 1, 2, 3 and 4 shorted together, and pins 5,6,7 and 8 shorted together

(**) 1.6mm below seating plane.

Electrical Characteristics (unless otherwise specified, Ta = 0~85°C, V_{CC} = 4.5~20V, I_{F(ON)} = 1.6~5mA, I_{F(OFF)} = 0~0.1mA, V_{EL} = 0~0.8V, V_{EH} = 2.0~20V)

Characteristic	Symbol	Test Condition		Min.	Typ.*	Max.	Unit
Output leakage current (V _O > V _{CC})	I _{OHH}	I _F = 5mA, V _{CC} = 4.5V	V _O = 5.5V	—	—	100	μA
			V _O = 20V	—	2	500	
Logic low output voltage	V _{OL}	I _{OL} = 6.4mA (4 TTL load)		—	0.32	0.5	V
Logic high output voltage	V _{OH}	I _{OH} = −2.6mA		2.4	3.4	—	V
Logic low enable current	I _{EL}	V _E = 0.4V		—	−0.13	−0.32	mA
Logic high enable current	I _{EH}	V _E = 2.7V		—	—	20	μA
		V _E = 5.5V		—	—	100	
		V _E = 20V		—	0.01	250	
Logic low enable voltage	V _{EL}	—		—	—	0.8	V
Logic high enable voltage	V _{EH}	—		2.0	—	—	V
Logic low supply current	I _{CCL}	I _F = 0mA V _E = don't care	V _{CC} = 5.5V	—	5	6.0	mA
			V _{CC} = 20V	—	5.6	7.5	
Logic high supply current	I _{CCH}	I _F = 5mA V _E = don't care	V _{CC} = 5.5V	—	2.5	4.5	mA
			V _{CC} = 20V	—	2.8	6.0	
High impedance state output current	I _{OZL}	I _F = 5mA V _E = 2V	V _O = 0.4V	—	1	−20	μA
			I _{OZH}	I _F = 0mA V _E = 2V	V _O = 2.4V	—	
	V _O = 5.5V	—			—	100	
	V _O = 20V	—			0.01	500	
Logic low short circuit output current (Note 4)	I _{OSL}	I _F = 0mA	V _O = V _{CC} = 5.5V	25	55	—	mA
			V _O = V _{CC} = 20V	40	80	—	
Logic high short circuit output current (Note 4)	I _{OSH}	I _F = 5mA V _O = GND	V _{CC} = 5.5V	−10	−25	—	mA
			V _{CC} = 20V	−25	−60	—	
Input current hysteresis	I _{HYS}	V _{CC} = 5V		—	0.05	—	mA
Input forward voltage	V _F	I _F = 5mA, Ta = 25°C		—	1.55	1.7	V
Temperature coefficient of forward voltage	ΔV _F / ΔTa	I _F = 5mA		—	−2.0	—	mV / °C
Input reverse breakdown voltage	BV _R	I _R = 10μA, Ta = 25°C		5	—	—	V
Input capacitance	C _{IN}	V _F = 0V, f = 1MHz, Ta = 25°C		—	45	—	pF
Resistance (input–output)	R _{I–O}	V _{I–O} = 500V R.H. ≤ 60% (Note 3)		5×10 ¹⁰	10 ¹⁴	—	Ω
Capacitance (input–output)	C _{I–O}	V _{I–O} = 0V, f = 1MHz (Note 3)		—	0.6	—	pF

(**) All typ. values are at Ta = 25°C, V_{CC} = 5V, I_{F(ON)} = 3mA unless otherwise specified.

Switching Characteristics

(unless otherwise specified, $T_a = 0\sim 85^\circ\text{C}$, $V_{CC} = 4.5\sim 20\text{V}$, $I_{F(ON)} = 1.6\sim 5\text{mA}$, $I_{F(OFF)} = 0\sim 0.1\text{mA}$)

Characteristic	Symbol	Test Circuit	Test Condition	Min.	Typ.	Max.	Unit
Propagation delay time to logic high output level (Note 5)	t_{pLH}	1	Without peaking capacitor C_1	—	235	—	ns
			With peaking capacitor C_1	—	—	400	
Propagation delay time to logic low output level (Note 5)	t_{pHL}		Without peaking capacitor C_1	—	250	—	ns
			With peaking capacitor C_1	—	—	400	
Output rise time (10–90%)	t_r		—	—	35	—	ns
Output fall time (90–10%)	t_f		—	—	20	—	ns
Output enable time to logic high	t_{pZH}	2	—	—	—	—	ns
Output enable time to logic low	t_{pZL}		—	—	—	—	ns
Output disable time from logic high	t_{pHZ}		—	—	—	—	ns
Output disable time from logic low	t_{pLZ}		—	—	—	—	ns
Common mode transient immunity at logic high output (Note 6)	CM_H	3	$I_F = 1.6\text{mA}$, $V_{CM} = 50\text{V}$, $T_a = 25^\circ\text{C}$	–1000	—	—	$\text{V} / \mu\text{s}$
Common mode transient immunity at logic low output (Note 6)	CM_L		$I_F = 0\text{mA}$, $V_{CM} = 50\text{V}$, $T_a = 25^\circ\text{C}$	1000	—	—	$\text{V} / \mu\text{s}$

(*) All typ. values are at $T_a = 25^\circ\text{C}$, $V_{CC} = 5\text{V}$, $I_{F(ON)} = 3\text{mA}$ unless otherwise specified.

(Note 4) Duration of output short circuit time should not exceed 10ms.

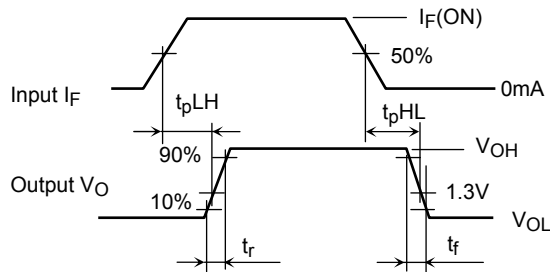
(Note 5) The t_{pLH} propagation delay is measured from the 50% point on the leading edge of the input pulse to the 1.3V point on the leading edge of the output pulse.

The t_{pHL} propagation delay is measured from the 50% point on the trailing edge of the input pulse to the 1.3V point on the trailing edge of the output pulse.

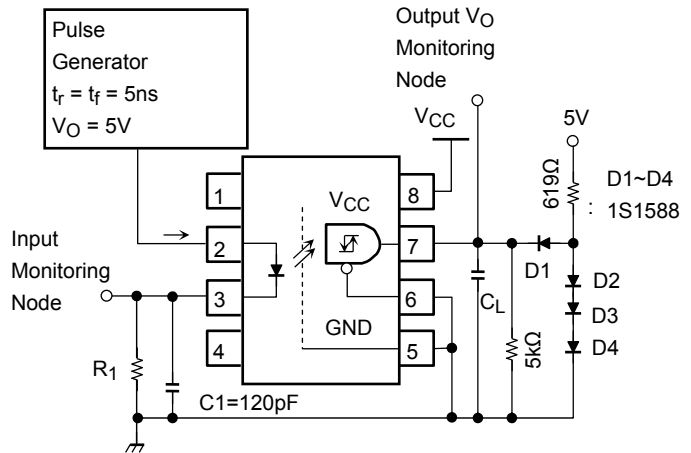
(Note 6) CM_L is the maximum rate of rise of the common mode voltage that can be sustained with the output voltage in the logic low state ($V_O \leq 0.8\text{V}$).

CM_H is the maximum rate of fall of the common mode voltage that can be sustained with the output voltage in the logic high state ($V_O \leq 2.0\text{V}$).

Test Circuit 1 t_{pHL} , t_{pLH} , t_r and t_f

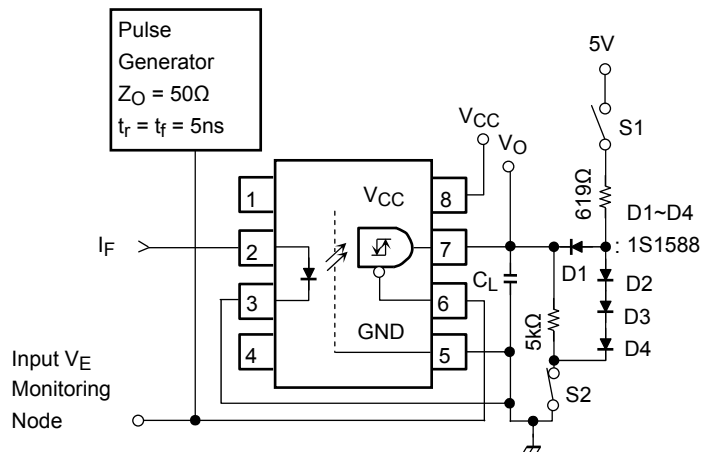
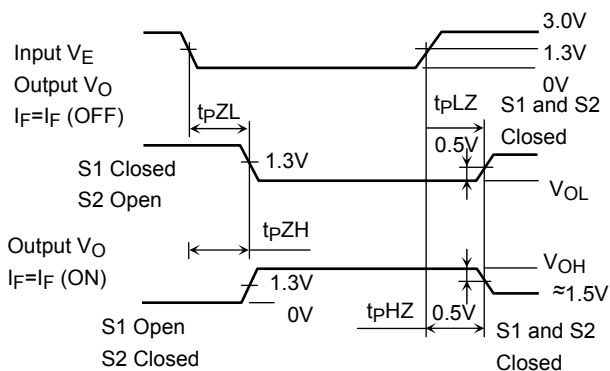


R_1	2.15k Ω	1.1k Ω	681 Ω
$I_F(ON)$	1.6mA	3mA	5mA



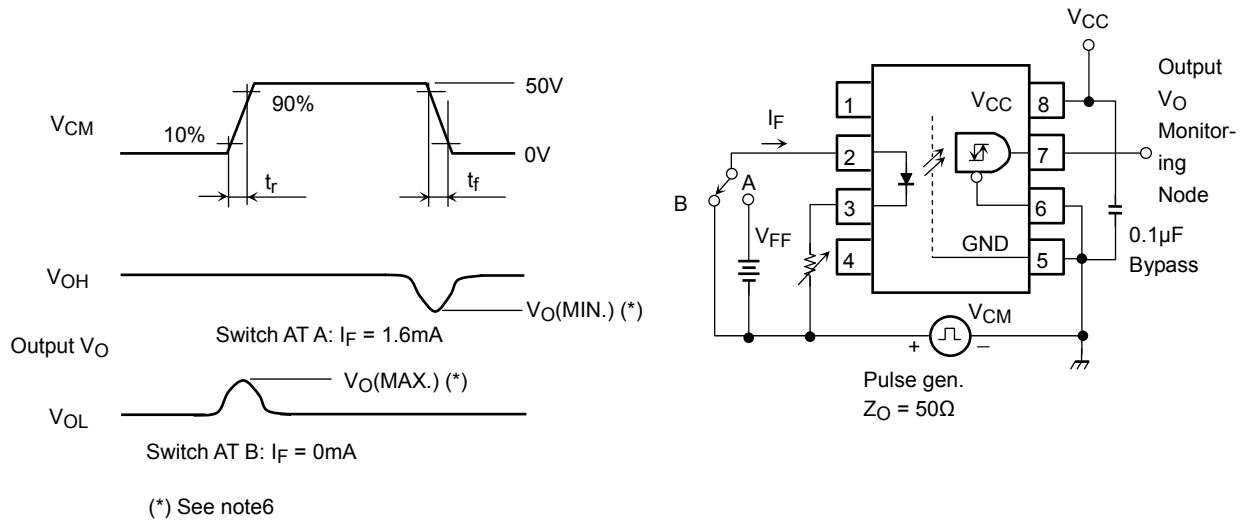
C_1 is peaking capacitor. The probe and jig capacitances are include in C_1 .
 C_L is approximately 15pF which includes probe and stray wiring capacitance.

Test Circuit 2 t_{pHZ} , t_{pZH} , t_{pLZ} and t_{pZL}



C_L is approximately 15pF which includes probe and stray wiring capacitance.

Test Circuit 3 Common Mode Transient Immunity



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